

# Emitter common (dual digital transistors)

## EMA11 / UMA11N / FMA11A

### ●Features

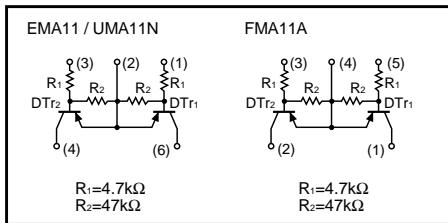
- 1) Two DTA143Z chips in a EMT or UMT or SMT package.
- 2) Mounting cost and area can be cut in half.

### ●Structure

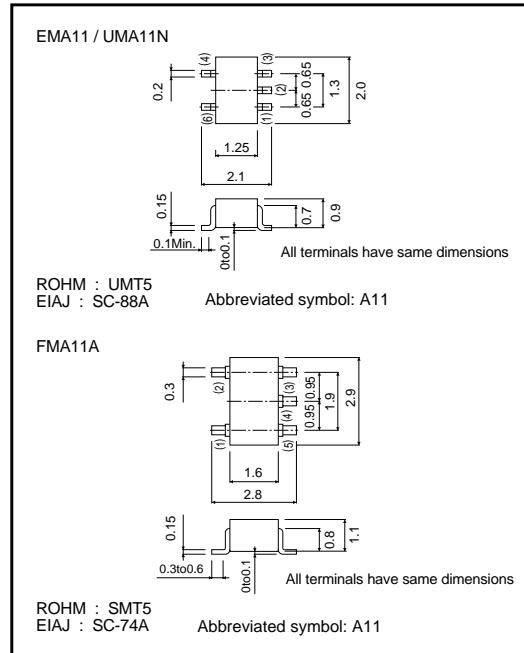
Epitaxial planar type  
PNP silicon transistor  
(Built-in resistor type)

The following characteristics apply to both DTr<sub>1</sub> and DTr<sub>2</sub>.

### ●Equivalent circuit



### ●External dimensions (Units : mm)



### ●Packaging specifications

Type	Package		Taping		
	Code		T2R	TR	T148
	Basic ordering unit (pieces)		8000	3000	3000
EMA11		○	—	—	—
UMA11N		—	○	—	—
FMA11A		—	—	○	—

### ●Absolute maximum ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Limits	Unit	
Supply voltage	V <sub>CC</sub>	-50	V	
Input voltage	V <sub>IN</sub>	-30 5	V	
Output current	I <sub>O</sub> I <sub>C</sub> (Max.)	-100 -100	mA	
Power dissipation	EMA11 / UMA11N FMA11A	P <sub>D</sub> 150 (TOTAL) 300 (TOTAL)	mW	*1 *2
Junction temperature	T <sub>j</sub>	150	°C	
Storage temperature	T <sub>STG</sub>	-55~+150	°C	

\*1 120mW per element must not be exceeded.

\*2 200mW per element must not be exceeded.

## Transistors

● Electrical characteristics ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	$V_{I(\text{off})}$	—	—	-0.5	V	$V_{CC}=-5\text{V}, I_O=-100\mu\text{A}$
	$V_{I(\text{on})}$	-1.3	—	—		$V_O=-0.3\text{V}, I_O=5\text{mA}$
Output voltage	$V_O(\text{on})$	—	-0.1	-0.3	V	$I_O/I_I=-5\text{mA}/-0.25\text{mA}$
Input current	$I_I$	—	—	-1.8	mA	$V_I=-5\text{V}$
Output current	$I_O(\text{off})$	—	—	-0.5	μA	$V_{CC}=-50\text{V}, V_I=0\text{V}$
DC current gain	$G_I$	80	—	—	—	$V_O=-5\text{V}, I_O=-10\text{mA}$
Transition frequency	$f_T$	—	250	—	MHz	$V_{CE}=10\text{mA}, I_E=5\text{mA}, f=100\text{MHz}$ *
Input resistance	$R_I$	3.29	4.7	6.11	kΩ	—
Resistance ratio	$R_2/R_1$	8	10	12	—	—

\* Transition frequency of the device

## ● Electrical characteristic curves

